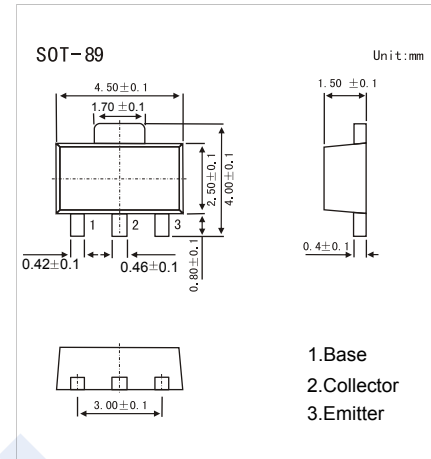
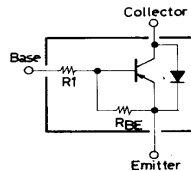


PNP Transistors

2SB1323-HF

■ Features

- Contains diode between collector and emitter.
- Low saturation voltage.
- Large current capacity.
- Complementary to 2SD1997-HF
- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V _{CB0}	-40	V
Collector - Emitter Voltage	V _{CE0}	-30	
Emitter - Base Voltage	V _{EB0}	-6	
Collector Current - Continuous	I _C	-3	A
Collector Current - Pulse	I _{CP}	-5	
Collector Power Dissipation	P _C	1.5	W
Junction Temperature	T _J	150	°C
Storage Temperature range	T _{stg}	-55 to 150	

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V _{CB0}	I _C = -100 μA, I _E =0	-40			V
Collector- emitter breakdown voltage	V _{CE0}	I _C = -10 mA, R _{BE} =∞	-30			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C =0	-6			
Collector-base cut-off current	I _{CB0}	V _{CB} = -35 V, I _E =0			-1	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-1 A, I _B =-50mA		-0.18	-0.4	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-1 A, I _B =-50mA			-1.2	
Base - emitter on voltage	V _{BE(on)}	V _{CE} = -2V, I _C = -1 A	-1		-5	
DC current gain	h _{FE(1)}	V _{CE} = -2V, I _C = -500mA	70			
	h _{FE(2)}	V _{CE} = -2V, I _C = -2 A	50			
Base-to-Emitter Resistance	R _{BE}			0.8		kΩ
Base Resistance	R ₁		120		200	Ω
Diode Forward Voltage	V _F	I _F =500mA			1.5	V
Collector output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz		55		pF
Transition frequency	f _T	V _{CE} = -5V, I _C = -500mA		150		MHz

■ Marking

Marking	BK F
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PNP Transistors

2SB1323-HF

■ Typical Characteristics

